

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	237302	(form\$3 same (gate or "gate electrode" or transistor)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 14:25			0
2	BRS	L2	20887	((cover\$3 or form\$3) with (trench)) same ("silicon oxide" or oxide or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:26			0
3	BRS	L3	15719	((cover\$3 or form\$3) with (trench)) with ("silicon oxide" or oxide or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:20			0
4	BRS	L4	14287	3 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:20			0
5	BRS	L5	20887	((cover\$3 or form\$3) with (trench)) same ("silicon oxide" or oxide or "SiO.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:29			0
6	BRS	L6	922	(cover\$3 or form\$3) with ("silicon oxide" or oxide or "SiO.sub.2") with ("with" or over) with (passivat\$3 or ("silicon nitride" or "SiN" or "Si.sub.3 N.sub.4") and ("SiC" or "silicon carbide"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:32			0
7	BRS	L7	956	5with 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 15:32			0
8	BRS	L8	124	5 and 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:07			0
9	BRS	L11	16	(sti or trench) same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:14			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BRS	L12	5	etch\$3 with (sti or trench) same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:16			0
11	BRS	L13	0	etch\$3 with (sti ) same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:15			0
12	BRS	L14	0	etch\$3 with ("shallow trench") same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:17			0
13	BRS	L15	8	etch\$3 same (sti or trench) same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:16			0
14	BRS	L16	0	etch\$3 same ("shallow trench") same (passivat\$ with ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:17			0
15	BRS	L17	509	etch\$3 same ("shallow trench") same (passivat\$ or ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:17			0
16	BRS	L18	1809	etch\$3 same ("shallow trench" or sti or trench) same (passivat\$ or ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:18			0
17	BRS	L19	622	etch\$3 with ("shallow trench" or sti or trench) with (passivat\$ or ((SiC or "silicon carbide") and (SiN or "silicon nitride" or "Si.sub.3 N.sub.4"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:18			0
18	BRS	L20	535	19 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/22 16:19			0